

of selective tungsten layers, said method comprising the steps of:

providing a silicon substrate;

forming a field oxide layer and a junction layer and gate electrode on said silicon substrate;

forming a first insulating layer on the whole structure;

forming first contact holes by removing **[the]** (desired) portions of the first insulating layer to expose said junction layer and gate electrode;

filling first metal layers into the first contact holes, entirely;

forming a conductive layer pattern on the first insulating layer spaced from said first metal layers;

forming a second insulating layer on the whole structure;

forming a **plurality of** second contact holes by removing **[the]** (desired) portions of said second insulating layer to expose both the first metal layers in said first contact holes and **[a] the** conductive layer **[spaced from said first contact hole] pattern**;

filling a second metal layer into said **plurality of** second contact holes to contact with the first metal layers and conductive layer **pattern, respectively; and**

wherein the first metal layer and second metal layer are both formed by chemical vapor deposition method.

In Claim 4, line 6, kindly replace "first" with --second--.

Kindly add new Claim 7 as follows:

7. (NEW) The method of claim 1, wherein the second insulating layer has a nonuniform thickness and a portion thereof is etched to result in the plurality of second contact holes of substantially equal depth, whereby a plurality of filled contact holes of different overall depths results after filling the second contact holes with second metal layers.

REMARKS

The undersigned attorney wishes to thank the Examiner for the courtesy extended to Mr.